

A2
concl. can apply to any structures, such as the existing p-Si coplanar structure, inverse-stagger structure and stagger structure.

Page 17, please amend the paragraph beginning at line 15 as follows:

A3
concl. Fig. 8 shows the configuration of the mask for the pixel portion with an inverse stagger structure, and Fig. 9 shows the cross section of A-B-C-D-E portions of the inverse stagger structure shown in Fig. 8. Because of the inverse stagger structure, the gate electrode 18 of the TFT exists on the lowest layer. The sampling capacitor 11 is formed between the common electrode 8 and the source electrode 19 of the sampling capacitor. By adopting such a structure, the insulating film of the sampling capacitor can be commonly used with a protection insulating film 57 of the sampling TFT. Therefore, it is possible to simplify the manufacturing process, making it suitable for a mass production in the currently main product.
